

FMOS3415

List

List..... 1

Package outline..... 2

Features..... 2

Mechanical data..... 2

Maximum ratings 2

Electrical characteristics..... 3

Rating and characteristic curves..... 4

Pinning information..... 5

Marking..... 5

Suggested solder pad layout..... 5

Packing information..... 6

Reel packing..... 7

Suggested thermal profiles for soldering processes..... 7

FMOS3415

20V P-Channel Enhancement Mode MOSFET

Features

- Excellent $R_{DS(ON)}$, low gate charge, low gate voltages
- Lead-free parts meet RoHS requirements
- Suffix "-H" indicates Halogen-free part, ex. FMOS3415-H

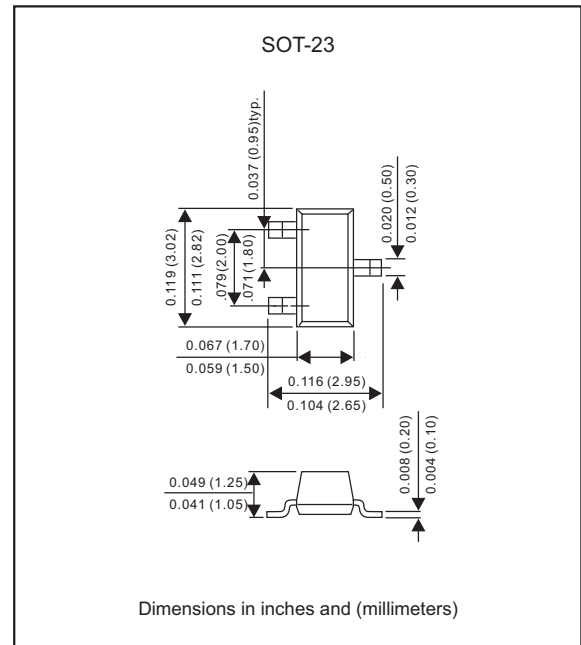
Applications

- Load switch and in PWM applications

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.008 gram

Package outline



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	-20	V
Gate-source voltage	V_{GS}	± 8	
Continuous drain current ($t \leq 10s$)	I_D	-4.0	A
Maximum power dissipation ($t \leq 10s$)	P_D	0.30	W
Thermal resistance from junction to ambient	$R_{\theta JA}$	417	$^{\circ}\text{C}/\text{W}$
Operating junction temperature range	T_J	-55 to +150	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^{\circ}\text{C}$

FMOS3415

Electrical characteristics (At $T_A=25^{\circ}\text{C}$ unless otherwise noted)

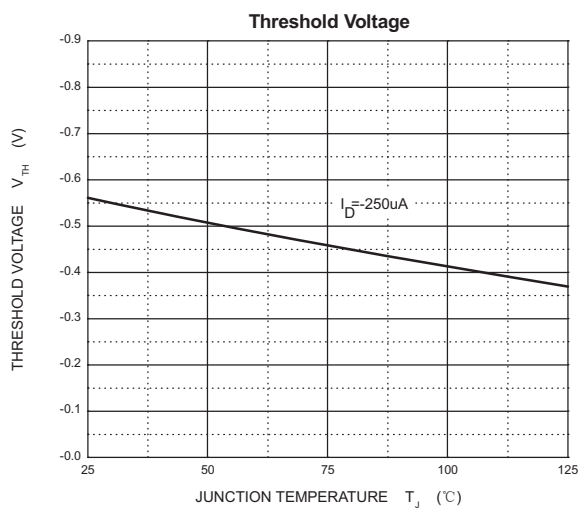
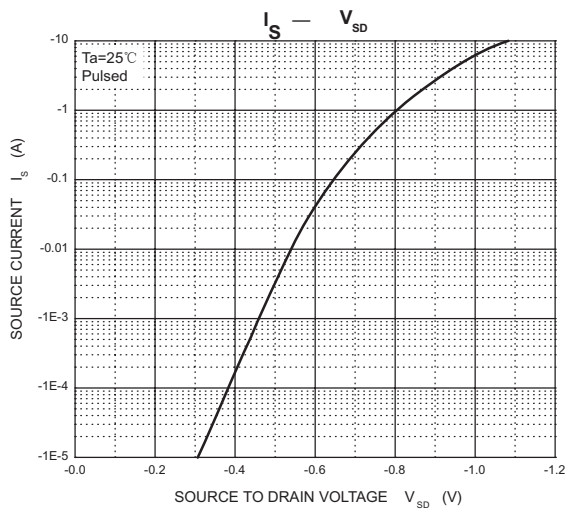
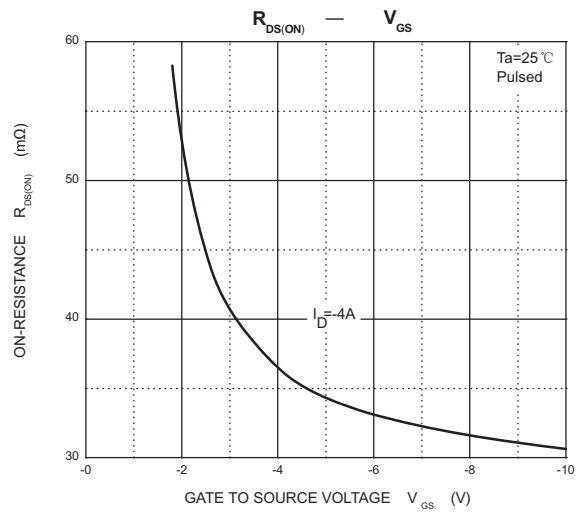
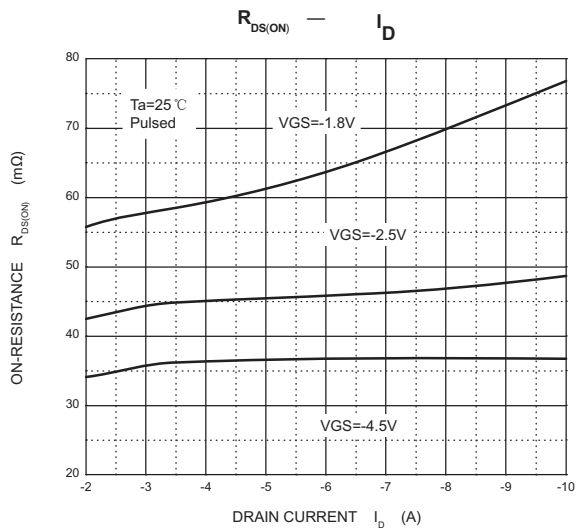
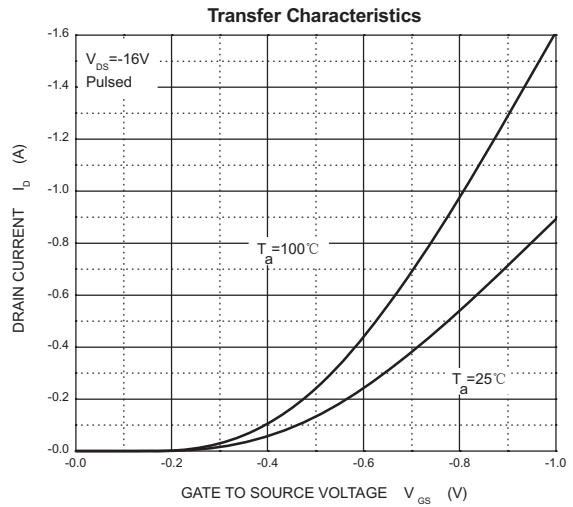
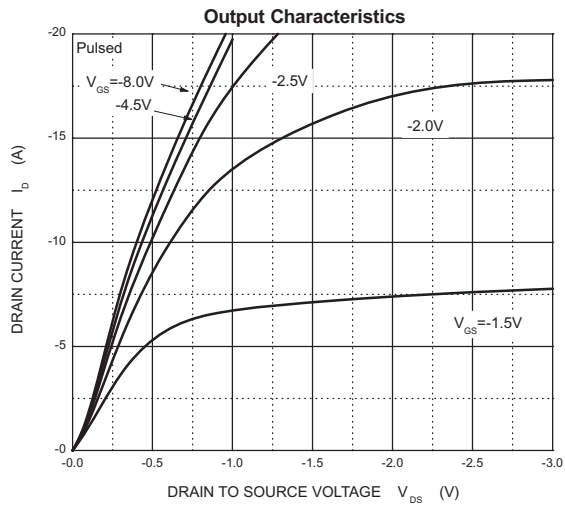
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Parameters						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.3	-0.56	-1	
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 10	μA
		$V_{DS} = 0V, V_{GS} = \pm 4.5V$			± 1	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1	
Drain-source on-state resistance(note2)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4A$		0.037	0.050	Ω
		$V_{GS} = -2.5V, I_D = -4A$		0.045	0.060	
		$V_{GS} = -1.8V, I_D = -2A$		0.056	0.073	
Forward transconductance(note2)	g_{FS}	$V_{DS} = -5V, I_D = -4A$	8			S
Body diode voltage(note2)	V_{SD}	$I_S = -1A, V_{GS} = 0V$			-1	V
Dynamic Parameters (note3)						
Input capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		1450		pF
Output capacitance	C_{oss}			205		
Reverse transfer capacitance	C_{rss}			160		
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		6.5		Ω
Switching Parameters						
Total gate charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -4A$		17.2		nC
Gate-source charge	Q_{gs}			1.3		
Gate-drain charge	Q_{gd}			4.5		
Turn-on delay time (note3)	$t_{d(on)}$	$V_{DS} = -10V, V_{GS} = -4.5V$ $R_{GEN} = 3\Omega, R_L = 2.5\Omega,$		9.5		ns
Turn-on rise time(note3)	t_r			17		
Turn-off delay time(note3)	$t_{d(off)}$			94		
Turn-off fall time(note3)	t_f			35		

Notes 1: Repetitive rating, pulse width limited by junction temperature

2: Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

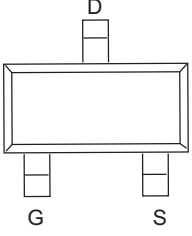
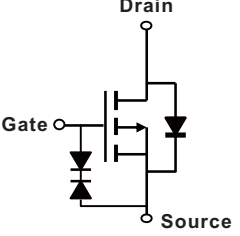
3: These parameters have no way to verify

Rating and characteristic curves (FMOS3415)



FMOS3415

Pinning information

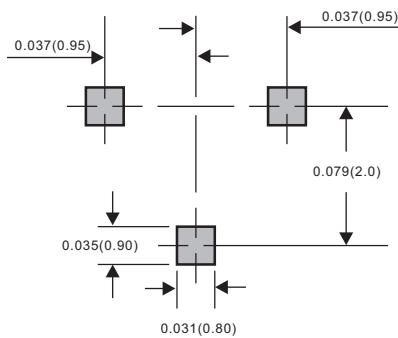
Pin	Simplified outline	Symbol
PinD Drain PinG Gate PinS Source		

Marking

Type number	Marking code
FMOS3415	R15

Suggested solder pad layout

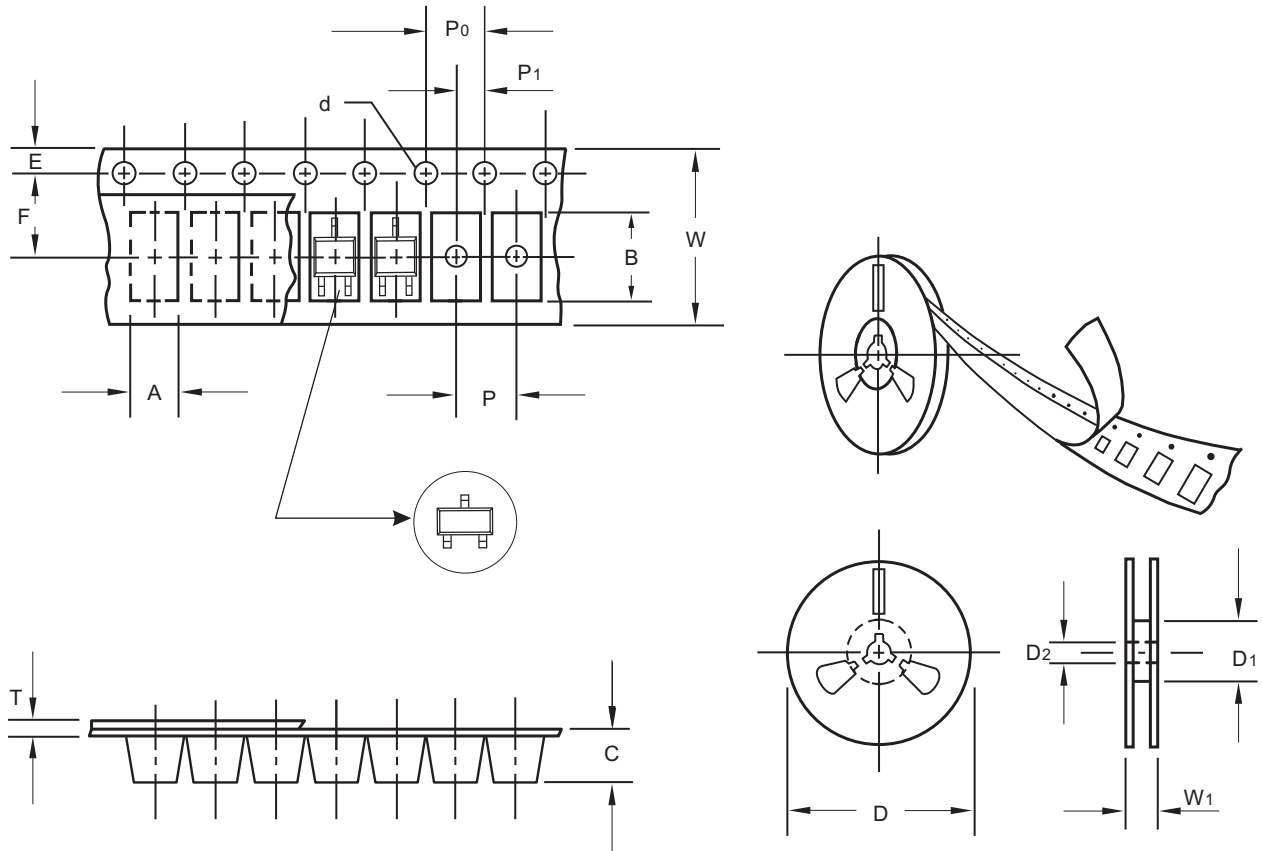
SOT-23



Dimensions in inches and (millimeters)

FMOS3415

Packing information



unit:mm

Item	Symbol	Tolerance	SOT-23
Carrier width	A	0.1	3.18
Carrier length	B	0.1	3.28
Carrier depth	C	0.1	1.32
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	60.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	12.0

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

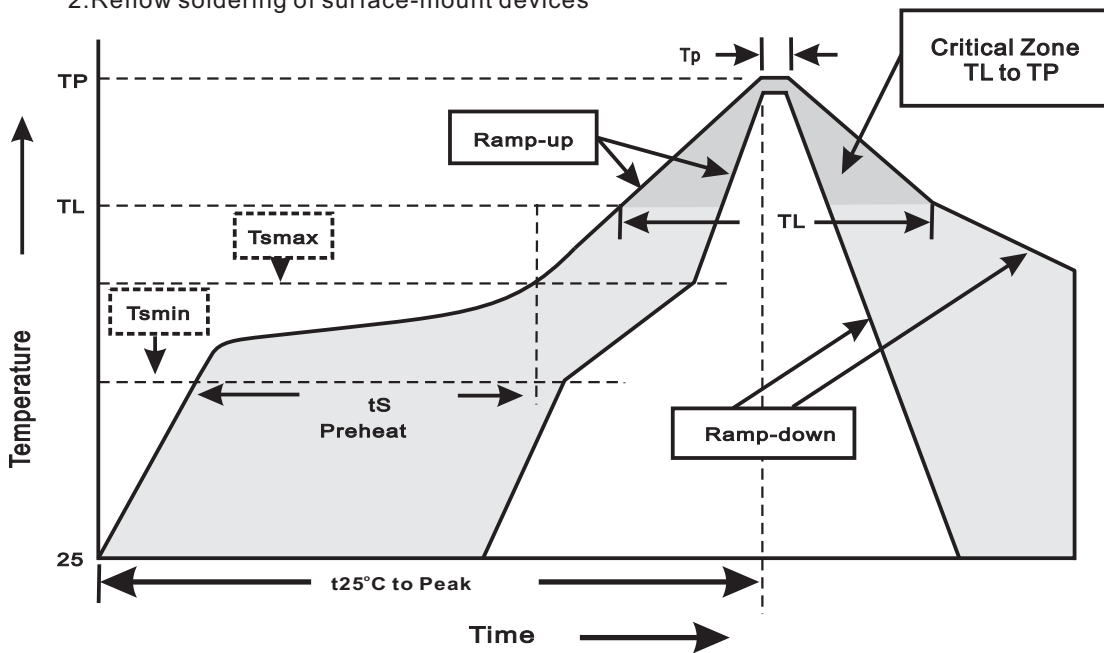
FMOS3415

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-23	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	11.6

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smin}) -Temperature Max(T _{smax}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smax} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes